

**FOR IMMEDIATE RELEASE**  
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*Leading GaN on Si RF power transistor manufacturer receives ISO 9001 certification...*

## **NITRONEX RECEIVES ISO 9001 QUALITY MANAGEMENT SYSTEMS- REQUIREMENTS REGISTRATION CERTIFICATION**

Durham, N.C. (November 19, 2007) — Nitronex, the global leader in gallium nitride on silicon (GaN on Si) RF power transistors for the wireless infrastructure, broadband and military markets, has received ISO 9001:2000 certification from Det Norske Veritas (DNV). The ISO 9001 certification verifies that Nitronex's Quality Management System meets the global standard and expectations.

"Achieving ISO 9001:2000 certification affirms our commitment to providing our customers with the highest quality gallium nitride on silicon RF power transistors," said Bruce Cochran, VP of Operations at Nitronex. "ISO certification is a significant milestone in our journey to become a mainstream supplier to the wireless, broadband and military industries."

ISO 9001 certification was developed by the International Organization for Standardization (ISO) to establish universal standards of operation for businesses. The rigorous standards are designed to help companies create and maintain specific procedures necessary to produce quality products and services.

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The successful ISO 9001:2000 qualification validates Nitronex's commitment to quality manufacturing and customer satisfaction.

For more information about Nitronex's GaN on Si manufacturing processes and broad product offering, contact Nitronex at 2305 Presidential Drive, Durham, NC 27703; call 919-807-9100; or e-mail [info@nitronex.com](mailto:info@nitronex.com).

### **About Nitronex**

Specializing in the development and manufacturing of gallium nitride (GaN) RF power devices, Nitronex is the global leader in high-performance GaN on silicon (GaN on Si) RF power transistors for the commercial wireless infrastructure, broadband and military markets. Based on its patented SIGANTIC<sup>®</sup> process — gallium nitride on silicon technology — Nitronex is at the forefront of commercializing GaN technology for RF applications. The company's ability to combine the disciplines of material growth, wafer processing, device design and wireless applications knowledge is unique to the industry.

Nitronex was founded in 1999 by graduates of the wide bandgap program at North Carolina State University and is headquartered in Durham, North Carolina. It holds 19 patents with 19 others pending.

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